

## SPECIFICATION

Please replace the paragraph beginning at page 1, line13 with the following:

A flash memory device is a nonvolatile high-density data storage device that can write and erase data [[on an]] on-board. A flash memory cell includes a field effect transistor (FET) having a selection gate, a floating gate, a source and a drain. Data is stored in the flash memory cell by variations in the amount of charge stored in the floating gate, which causes a variation in a threshold voltage ( $V_t$ ) of the flash memory cell. The data stored in the flash memory cell is read out by applying a selection voltage to a word line connected to the selection gate. The amount of current, which flows when the flash memory cell is selected, is determined by the threshold voltage ( $V_t$ ) of the flash memory cell.